Figure 5 (a) Cross-sectional SEM images of silicon samples etched in the solution containing 4.6 M HF, 0.02 M AgNO$_3$, and 0.005 M KMnO$_4$ for 45min; (b) Cross-sectional SEM images of n-Si(100) with the resistivity of 3-5 $\Omega \cdot$cm etched in the solution containing 4.6 M HF, 0.02 M AgNO$_3$, and 0.05 M KMnO$_4$ for 45min.